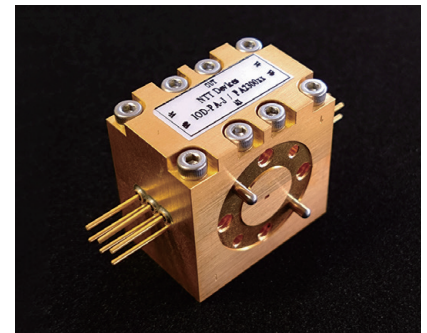


220-330GHz-Band Power Amplifier

This power amplifier provides a power gain of 10 dB in the J-band frequency range (220-320 GHz) and a saturated output power of 8 dBm.

An InP-based heterojunction bipolar transistor (InP HBT) IC technology is applied to realize the high frequency and high output power performance. It has an easy-to-use module configuration in which the WR-03 waveguide can be connected to the input / output port.

The amplifier is suitable to boost the power of J-band millimeter wave signals in transceivers for wireless communications systems or sensing systems.



FEATURES

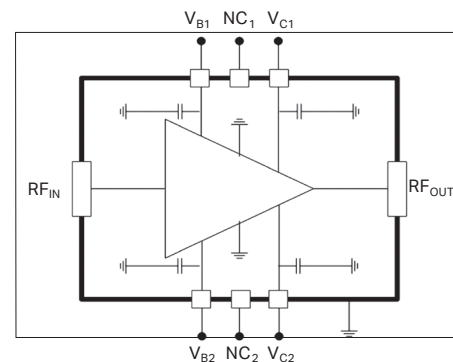
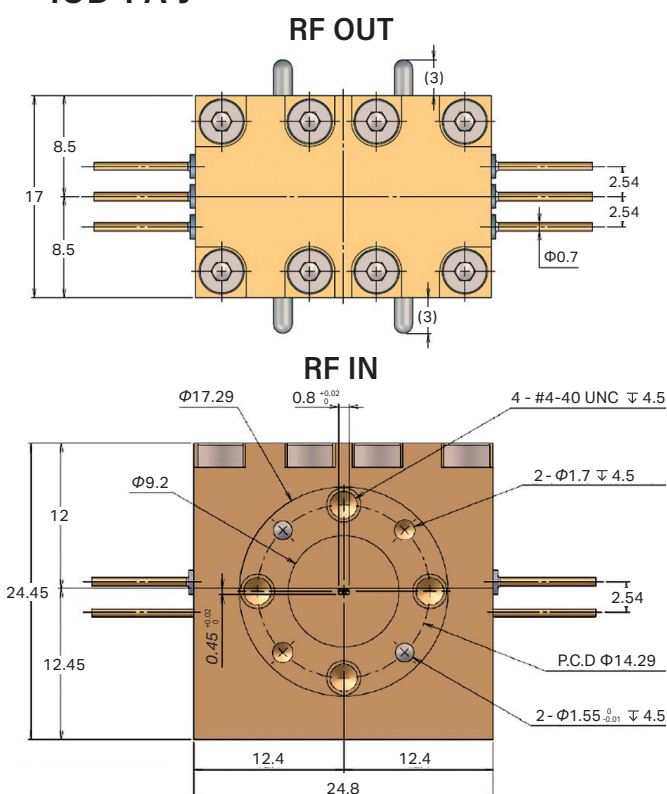
- J-band (220-330GHz) waveguide module with WR-3.4
- Waveguide with UG-387/U-M Anti-Cocking Flange.
- High gain of over 10 dB in the J-band frequency range
- High saturation output power of 10dBm

SPECIFICATIONS

Item	Specifications *Tentative value
Power Supply Voltage	1.5V / 0.96V
Power Supply Current	Typ 361mA / 6mA*
Powe dissipation	Max 700mW
RF input / output	Max 6dBm / 10dBm
BW	220-330GHz (S21>10dB)
Gain	6dB-22dB (220-330GHz)

OUTSIDE DIMENSIONS

IOD-PA-J



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Sensing application
website